DARLINGTON PHOTO TRANSISTOR 204-0676-90 D113

DESCRIPTION

A Darlington photo transistor made using the standard 200 Ω/sq process. The emitter is internally shorted to the substrate while the collectors are isolated so that it may be scribed into common emitter arrays. The device is normally operated open base but a base contact pad is provided. The device responds to visible and infrared radiation with a peak efficiency around 0.7 μm.

Composite Beta (6 Volts, 1 mA)	1,600 to 10,000
I_{CEO} (Dark, V_{CE} = 8 Volts)	<0.1 μA
BV_{CEO} (10 μA) Typical	15 Volts
I_{MAX}	> 5 mA
V_{CESAT} (1 mA) Typical	1.1 Volt

PROCESS	200 Ω/Sq
DESIGNER	Bob Nordstrom
INSTRUMENT USAGE	